

The most efficient low V_{CEsat} (BISS) transistors

Experience best performance for on-state-resistance and switching times. Choose from NXP's broad portfolio of energy and space saving products.



Low V_{CEsat} (BISS) transistors

Our efficient low V_{CEsat} transistors live up to their name as Breakthrough In Small Signal (BISS) transistors. They offer lower power losses with higher efficiency than their standard transistor counterparts, and they deliver the required performance in smaller packages that save PCB space. Choose from single and double transistors, resistor-equipped transistors (RETs), or load switches, which combine a low V_{CEsat} transistor with a RET in a single package.

Key features

- ▶ Low V_{CEsat} and high current capability
- ▶ Broad portfolio supports all kinds of applications
- ▶ Wide voltage range, including high-voltage types up to 500 V

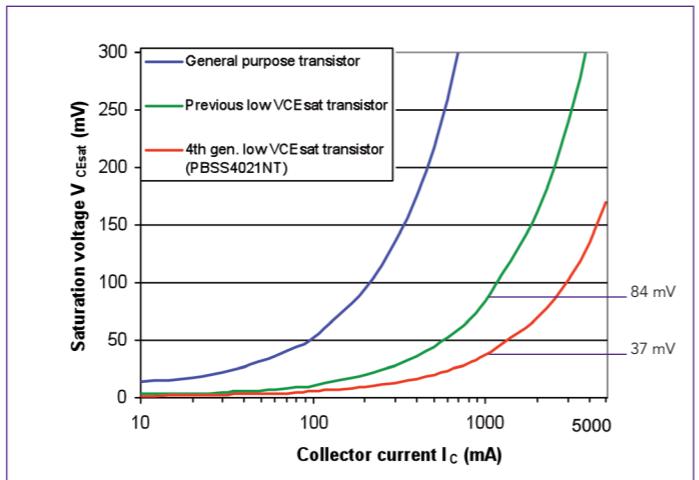
Key benefits

- ▶ Optimum power performance while saving space
- ▶ Very small packages enable integration of more functions onto a PCB
- ▶ Less heat generation
- ▶ Energy saving
- ▶ Fewer components by using modules like RETs, double transistors, and load switches
 - Simpler circuit layouts
 - Lower pick-and-place costs
 - Less board space

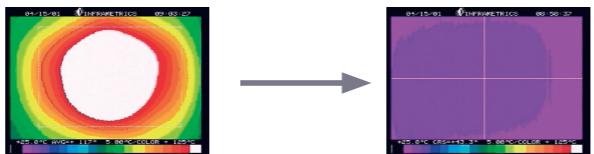
Applications

- ▶ Portable applications (mobile phones, DSCs, PDAs, etc.)
- ▶ Power management
- ▶ Load switches
- ▶ Battery chargers
- ▶ DC/DC converter
- ▶ LED driver circuits in LCD backlight units

Reduced power dissipation due to low V_{CEsat}



65 % heat reduction by BISS transistors



General purpose transistor $T_{case} = 110^\circ\text{C}$

High performance BISS transistor $T_{case} = 40^\circ\text{C}$

Temperature profile of device surface (T_{case}). Comparison of a general purpose transistor and a BISS transistor.

We have shipped more than 1 billion low V_{CEsat} (BISS) transistors. Our portfolio, now in its fourth generation, has been designed into all kinds of applications and is used by most of the top manufacturers

Product News: Fourth-generation technology

Our new, highly efficient 4th generation low V_{CEsat} (BISS) transistors are available in two optimized versions - an ultra-low V_{CEsat} and a high-speed switching version.

The products are available in small SMD packages SOT23, SOT457 (SC-74), SOT89 (SC-62) and SOT223 (SC-73) for single and SOT96 (SO-8) for double transistors.

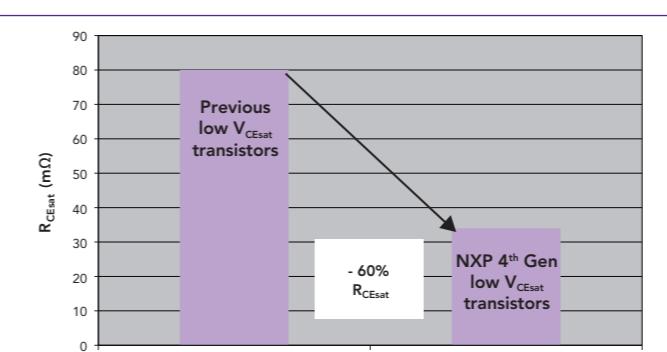
Ultra-low V_{CEsat} devices optimized for load-switch applications

- ▶ These devices introduce a new ultra-low-ohmic substrate technology and a patented chip metallization architecture
- ▶ Ultra-low saturation voltage due to on-state-resistance reduced by 60% compared to previous generations of low V_{CEsat} transistors.

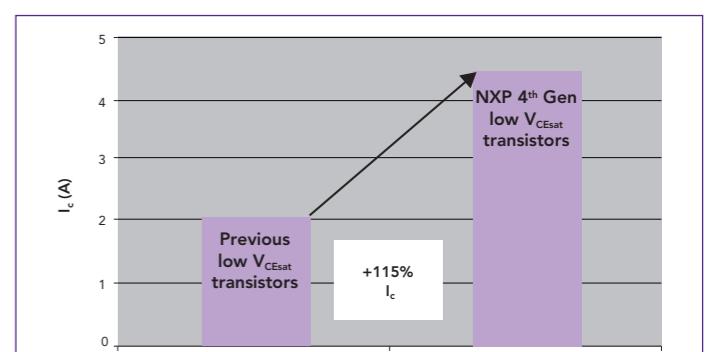
- ▶ Electrical performance for low-loss load switching comparable to available products with twice the size due to doubled maximum current capability I_c (+115%)

- ▶ Available in 20 V and 60 V versions

Ultra-low on-state-resistance



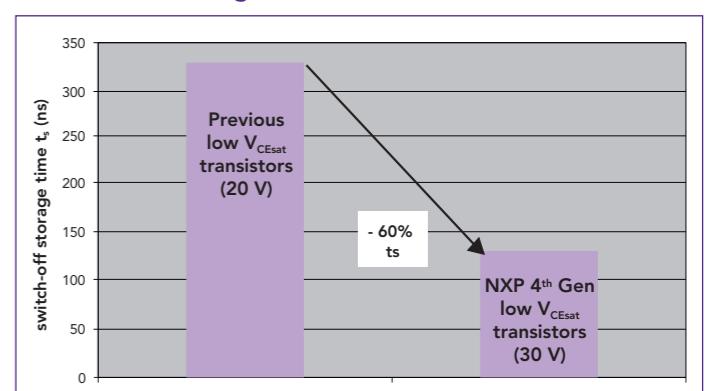
High current capability



Low V_{CEsat} devices optimized for high-speed switching applications

- ▶ These devices introduce a new design that combines MESH-emitter technology with base contact extraction electrodes.
- ▶ Low on-state resistance down to 50 mΩ, combining high switching performance with minimized saturation voltages and power dissipation – an industry first
- ▶ Switching time (t_s) minimized by 60%.

Minimized switching times



Product overview - Ultra-low V_{CEsat} devices, optimized for load-switch applications

Single transistors

Type	Package	Polarity	V_{CEO} (V)	I_c (A)	I_{CM} (A)	$RCEsat\ typ\ (m\Omega)\ @ I_c; I_c/I_b = 10$
PBSS4021NT	SOT23	NPN	20	4.3	8	36
PBSS4021NX	SOT89 (SC-62)			7	15	19
PBSS4021NZ	SOT223 (SC-73)			8	20	14
PBSS4021PT	SOT23			3.5	8	55
PBSS4021PX	SOT89 (SC-62)	PNP	20	6.2	15	23
PBSS4021PZ	SOT223 (SC-73)			6.6	20	22
PBSS4041NT	SOT23			3.8	8	46
PBSS4041NX	SOT89 (SC-62)			6.2	15	25
PBSS4041NZ	SOT223 (SC-73)			7	15	17.5
PBSS4041PT	SOT23			2.7	8	80
PBSS4041PX	SOT89 (SC-62)	NPN	60	5	15	40
PBSS4041PZ	SOT223 (SC-73)			5.7	15	29

Double transistors

Type	Package	Polarity	V_{CEO} (V)	I_c (A)	I_{CM} (A)	$RCEsat\ typ\ (m\Omega)\ @ I_c; I_c/I_b = 10$
PBSS4021SN	SOT96 (SO8)	NPN/NPN	20	7.5	15	25
PBSS4021SPN		NPN/PNP		7.5/6.3	15	25/36
PBSS4021SP		PNP/PNP		6.3	15	36
PBSS4041SN		NPN/NPN	60	6.7	15	32
PBSS4041SPN		NPN/PNP		6.7/5.9	15/10	32/47
PBSS4041SP		PNP/PNP		5.9	10	47

Product overview - Low V_{CEsat} devices, optimized for high-speed switching applications

Single transistors

Type	Package	Polarity	V_{CEO} (V)	I_c (A)	I_{CM} (A)	$RCEsat\ typ\ (m\Omega)\ @ I_c; I_c/I_b = 10$
PBSS4032NT	SOT23	NPN	30	2.6	5	76
PBSS4032ND	SOT457 (SC-74)			3.5	6	50
PBSS4032NX	SOT89 (SC-62)			4.7	10	45
PBSS4032NZ	SOT223 (SC-73)			4.9	10	45
PBSS4032PT	SOT23	PNP	30	2.4	5	110
PBSS4032PD	SOT457 (SC-74)			2.7	5	88
PBSS4032PX	SOT89 (SC-62)			4.2	10	58
PBSS4032PZ	SOT223 (SC-73)			4.4	10	58

Double transistors

Type	Package	Polarity	V_{CEO} (V)	I_c (A)	I_{CM} (A)	$RCEsat\ typ\ (m\Omega)\ @ I_c; I_c/I_b = 10$
PBSS4032SN	SOT96 (SO8)	NPN/NPN	30	5.7	10	45
PBSS4032SP		PNP/PNP		4.8	10	65
PBSS4032SPN		NPN/PNP		5.7/4.8	10	45/65

Package overview with body size



SOT23
2.9 x 1.3 x 1.0 mm

SOT457 (SC-74)
2.9 x 1.5 x 1.0 mm

SOT89 (SC-62)
4.5 x 2.5 x 1.5 mm

SOT223 (SC-73)
6.5 x 3.5 x 1.65 mm

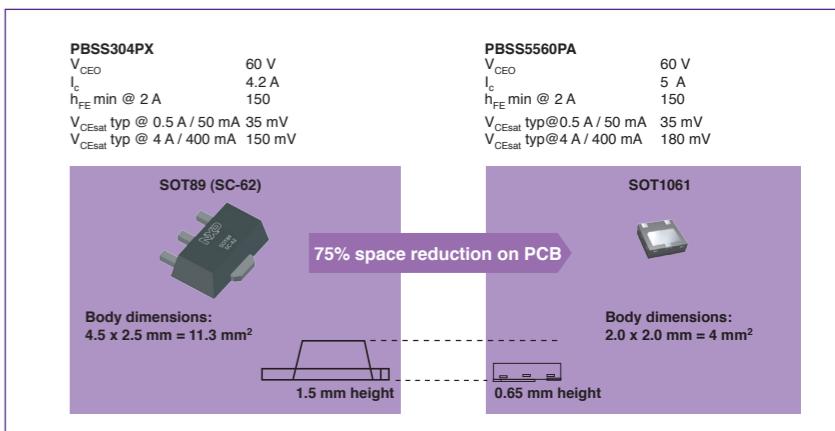
SOT96 (SO8)
4.9 x 3.9 x 1.75 mm

Product News: Low V_{CEsat} (BISS) transistors in SOT1061 package

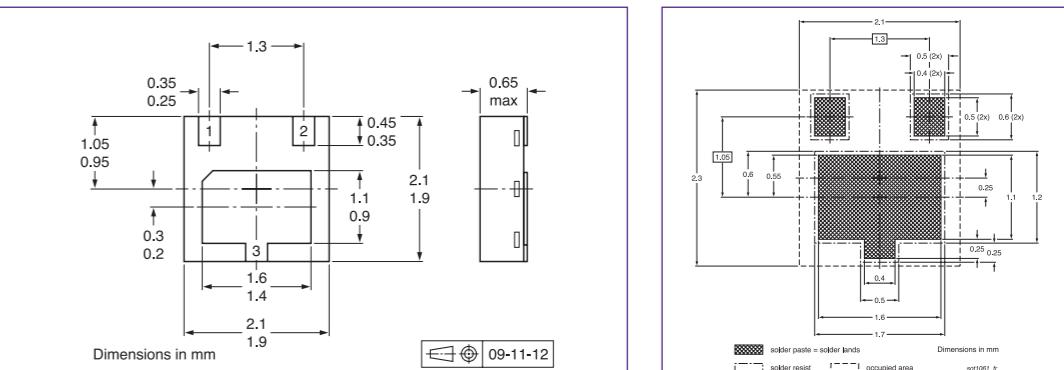
Key features

- Exposed heat sink for excellent thermal and electrical conductivity
- Power dissipation capability (P_{tot}) of > 1 W
- Small footprint of 2 x 2 mm and height of 0.65 mm
- Ideal for mobile and battery-driven applications

Performance comparison SOT1061 versus SOT89



SOT1061 minimized outline and solder pattern



Low V_{CEsat} (BISS) transistors in SOT1061

Type	Polarity	V_{CEO} (V)	I_c (A)	I_{CM} (A)	h_{FE} (min/typ)	$R_{CEsat}\ typ\ (m\Omega)\ @ I_c; I_c/I_b = 20$	$V_{CEsat}\ typ\ (mV)\ @ I_c=0,5\ A; I_b=50\ mA$	$V_{CEsat}\ max\ (mV)\ @ I_c; I_c/I_b = 20$
PBSS4612PA	NPN	12	6.0	7.0	280/440	33	20	275
PBSS4620PA		20	6.0	7.0	280/440	33	20	275
PBSS4330PA		30	3.0	5.0	300/465	75*	40	300*
PBSS4630PA		30	6.0	7.0	280/450	35	21	275
PBSS4560PA		60	6.0	7.0	280/440	34	22	290
PBSS4580PA		80	5.6	7.0	270/425	40	25	320
PBSS8510PA	PNP	100	5.2	6.0	180/285	48	30	340
PBSS5612PA		12	6.0	7.0	220/335	33	20	300
PBSS5620PA		20	6.0	7.0	230/345	39	25	350
PBSS5330PA		30	3.0	5.0	200/320	75*	45	320*
PBSS5630PA		30	6.0	7.0	230/345	39	25	350
PBSS5560PA		60	5.0	6.0	180/265	35	35	450
PBSS5580PA		80	4.0	5.0	180/265	65	40	420
PBSS9410PA		100	2.7	4.0	180/295	110	45	450

* IC/IB = 10

High voltage low V_{CESat} (BISS) transistors

types in **bold** represent new products

Package				SOT223 (SC-73)	SOT89 (SC-62)	SOT23
						
Size (mm)				6.5 x 3.5 x 1.65	4.5 x 2.5 x 1.5	2.9 x 1.3 x 1.0
P _{tot} (mW)				1700	1300	250
Polarity	V _{CESM} ¹⁾	V _{CEO} (V)	I _c (A)			
NPN	-	150	1	PBHV8115Z		PBHV8115T
			2	PBHV8215Z		
	500	400	0.5	PBHV8540Z		PBHV8540T
			1	PBHV8140Z		
		500	0.15			PMBTA45
PNP	-	150	0.4	PBHV8550Z		
			1	PBHV9115Z	PBHV9115X	PBHV9115T
	500	400	2	PBHV9215Z		
			0.25	PBHV9040Z		PBHV9040T
		500	0.5	PBHV9540Z		
			0.15			PBHV9050T
			0.25	PBHV9050Z		

¹⁾ Collector-emitter peak voltage

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